

# Yun Zhang

## List of Publications by Year in descending order

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Version: 2024-02-01

20  
papers

637  
citations

759233

12  
h-index

839539

18  
g-index

20  
all docs

20  
docs citations

20  
times ranked

777  
citing authors

#	ARTICLE	IF	CITATIONS
1	282-nm AlGaIn-based deep ultraviolet light-emitting diodes with improved performance on nano-patterned sapphire substrates. Applied Physics Letters, 2013, 102, .	3.3	184
2	Integrated High-Q Crystalline AlN Microresonators for Broadband Kerr and Raman Frequency Combs. ACS Photonics, 2018, 5, 1943-1950.	6.6	71
3	AlGaIn-based deep ultraviolet light-emitting diodes grown on nano-patterned sapphire substrates with significant improvement in internal quantum efficiency. Journal of Crystal Growth, 2014, 395, 9-13.	1.5	68
4	Integrated continuous-wave aluminum nitride Raman laser. Optica, 2017, 4, 893.	9.3	54
5	Aluminum nitride-on-sapphire platform for integrated high-Q microresonators. Optics Express, 2017, 25, 587.	3.4	48
6	AlGaIn-based ultraviolet light-emitting diode on high-temperature annealed sputtered AlN template. Journal of Alloys and Compounds, 2019, 794, 8-12.	5.5	32
7	Broadband tunable microwave photonic phase shifter with low RF power variation in a high-Q AlN microring. Optics Letters, 2016, 41, 3599.	3.3	31
8	Crystal quality improvement of sputtered AlN film on sapphire substrate by high-temperature annealing. Journal of Materials Science: Materials in Electronics, 2018, 29, 13766-13773.	2.2	29
9	Generation of multiple near-visible comb lines in an AlN microring via $\chi^{(2)}$ and $\chi^{(3)}$ optical nonlinearities. Applied Physics Letters, 2018, 113, .	3.3	25
10	Stimulated emission at 272 nm from an Al <sub>x</sub> Ga <sub>1-x</sub> N-based multiple-quantum-well laser with two-step etched facets. RSC Advances, 2016, 6, 50245-50249.	3.6	14
11	Enhanced performance of AlN SAW devices with wave propagation along the $\Gamma$ -K direction on $\chi$ -plane sapphire substrate. Journal Physics D: Applied Physics, 2019, 52, 215103.	2.8	14
12	Reducing stimulated emission threshold power density of AlGaIn/AlN multiple quantum wells by nano-trench-patterned AlN template. Journal of Alloys and Compounds, 2019, 777, 344-349.	5.5	13
13	Deep-ultraviolet stimulated emission from AlGaIn/AlN multiple-quantum-wells on nano-patterned AlN/sapphire templates with reduced threshold power density. Journal of Alloys and Compounds, 2017, 723, 192-196.	5.5	10
14	AlGaIn-based ultraviolet light-emitting diodes on sputter-deposited AlN templates with epitaxial AlN/AlGaIn superlattices. Superlattices and Microstructures, 2018, 113, 713-719.	3.1	10
15	Method of the out-of-band rejection improvement of the AlN based surface acoustic wave filters. Ultrasonics, 2019, 91, 30-33.	3.9	10
16	Structural characterization of AlN (11-22) films prepared by sputtering and thermal annealing on m-plane sapphire substrates. Superlattices and Microstructures, 2020, 141, 106493.	3.1	9
17	Optimization of selective-area regrown n-GaN via MOCVD for high-frequency HEMT. Applied Physics Letters, 2021, 119, .	3.3	8
18	Semi-polar (11-22) AlN epitaxial films on m-plane sapphire substrates with greatly improved crystalline quality obtained by high-temperature annealing. Journal of Crystal Growth, 2021, 570, 126207.	1.5	6

#	ARTICLE	IF	CITATIONS
19	Broadband visible comb generation in AlN-on-sapphire microresonators. , 2017, , .		1
20	High-resistance GaN-based buffer layers grown by a polarization doping method. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 307-310.	0.8	0